



BTA20-800CW

Three quadrant triacs

HAOPIN MICROELECTRONICS CO.,LTD.

Description

Passivated high commutation triacs in a plastic envelope intended for use in circuits where high static and dynamic dV/dt and high dI/dt can occur. These devices will commutate the full rated ms current at the maximum rated junction temperature without the aid of a snubber.

Symbol	Simplified outline
Pin	Description
1	Main terminal 1 (T1)
2	Main terminal 2 (T2)
3	gate (G)
TAB	isolated

Applications:

- ◆ Motor control
- ◆ Industrial and domestic lighting
- ◆ Heating
- ◆ Static switching

Features

- ◆ Blocking voltage to 800 V
- ◆ On-state RMS current to 20 A

SYMBOL	PARAMETER	Value	Unit
V_{DRM}	Repetitive peak off-state voltages	800	V
$I_T \text{ (RMS)}$	RMS on-state current (full sine wave)	20	A
I_{TSM}	Non-repetitive peak on-state current (full cycle, $T_j \text{ initial} = 25^\circ\text{C}$)	200	A

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$R_{th(j-c)}$	Junction to case(AC)		-	2.1	-	°C/W
$R_{th(j-a)}$	Junction to ambient		-	60	-	°C/W



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Limiting values in accordance with the Maximum system(IEC 134)

SYMBOL	PARAMETER	CONDITIONS		MAX	Value	UNIT		
V_{DRM}	Repetitive peak off-state Voltages	$T_j=125^\circ C$		-	800	V		
$I_{T(RMS)}$	RMS on-state current	360° conduction angle		$T_c=70^\circ C$	-	A		
I_{TSM}	Non repetitive surge peak on-state current	$T_j \text{ initial}=25^\circ C$		$t_p=8.3\text{ms}$	-	A		
				$t_p=10\text{ms}$	-	A		
I^2t	I^2t value	$T_p=10\text{ms}$		-	200	A^2s		
DI/dt	Critical rate of rise of on-state current	Gate supply: $I_g=500\text{mA}$ $dI_g/dt=1\text{A}/\mu\text{s}$	Repetitive $F=50\text{Hz}$	-	20	$\text{A}/\mu\text{s}$		
			Non repetitive	-	100			
I_{DRM}	V_{DRM} rated	$T_j=25^\circ C$		0.01	-	mA		
I_{RRM}	V_{RRM} rated	$T_j=125^\circ C$		3	-	mA		
T_I	Maximum lead soldering temperature during 10s at 4.5mm form case			-	260	$^\circ C$		
T_{sg}	Storage and operating junction temperature range			-40	150	$^\circ C$		
T_j	Storage and operating junction temperature range			-40	125	$^\circ C$		

$T_j=25^\circ C$ unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
Static characteristics						
I_{GT}						
V_{GT}	$V_D=12V(\text{DC})$; $R_L=33\Omega$	$T_j=25^\circ C$	I-II-III	1	-	35 mA
			I-II-III	-	-	1.5 V
I_L	$I_g=1.2 I_{GT}$	$T_j=25^\circ C$	I-III	-	-	- mA
			II	-	-	-
			I-II-III	-	-	80
I_H	$I_T=500\text{mA}$ Gate open	$T_j=25^\circ C$	-	-	50	mA
V_{GD}	$V_D=V_{DRM}$ $R_L=3.3K\Omega$	$T_j=125^\circ C$	I-II-III	0.2	-	- V
dV/dt	$V_D=67\%V_{DRM}$ gate open;	$T_j=125^\circ C$		250	500	- $\text{V}/\mu\text{s}$
$(dv/dt)c$	Without snubber	$T_j=125^\circ C$		11	22	- A/ms

Dynamic Characteristics

$V_{TM}(2)$	$I_{TM}=28\text{A}$ $t_p=380\mu\text{s}$	$T_j=25^\circ C$	-	-	1.70	V
tgt	$V_D=V_{DRM}$ $I_g=500\text{mA}$ $dI_g/dt=3\text{A}/\mu\text{s}$	$T_j=25^\circ C$	I-II-III	-	2	μs

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Fig. 1: Maximum RMS power dissipation versus RMS on-state current ($F = 50\text{Hz}$). (Curves are cut off by $(dI/dt)_c$ limitation)

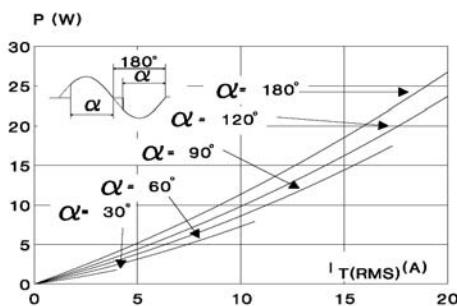


Fig. 2: Correlation between maximum RMS power dissipation and maximum allowable temperatures (T_{amb} and T_{case}) for different thermal resistances heatsink + contact (BTA).

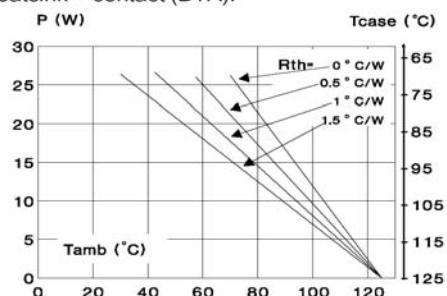


Fig. 3: Correlation between maximum RMS power dissipation and maximum allowable temperatures (T_{amb} and T_{case}) for different thermal resistances heatsink + contact (BTB).

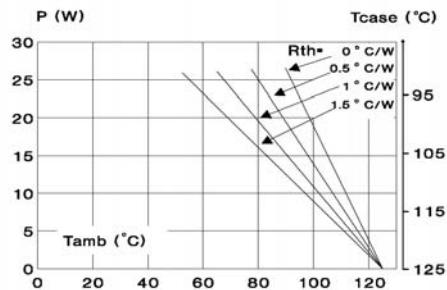


Fig. 4: RMS on-state current versus case temperature.

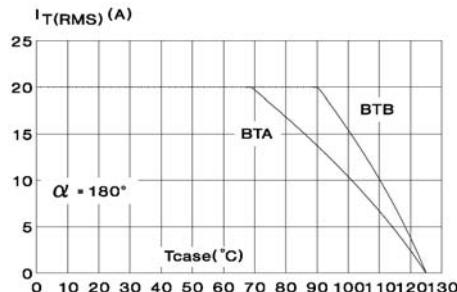


Fig. 5: Relative variation of thermal impedance versus pulse duration.

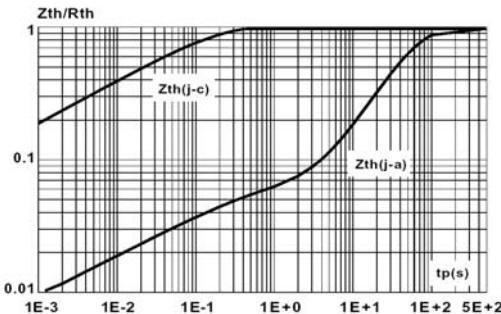
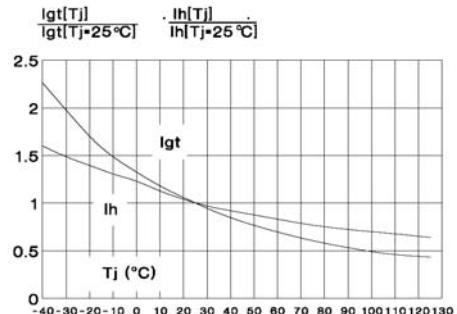


Fig. 6: Relative variation of gate trigger current and holding current versus junction temperature.



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Fig. 7: Non repetitive surge peak on-state current versus number of cycles.

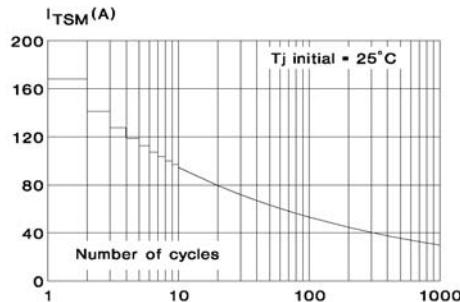


Fig. 8: Non repetitive surge peak on-state current for a sinusoidal pulse with width: $t \leq 10\text{ms}$, and corresponding value of I^2t .

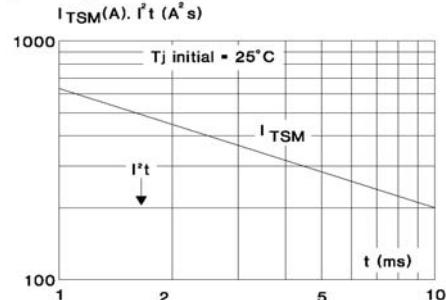
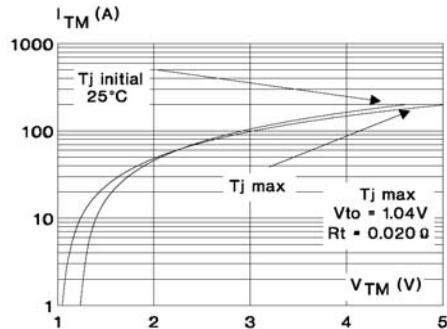
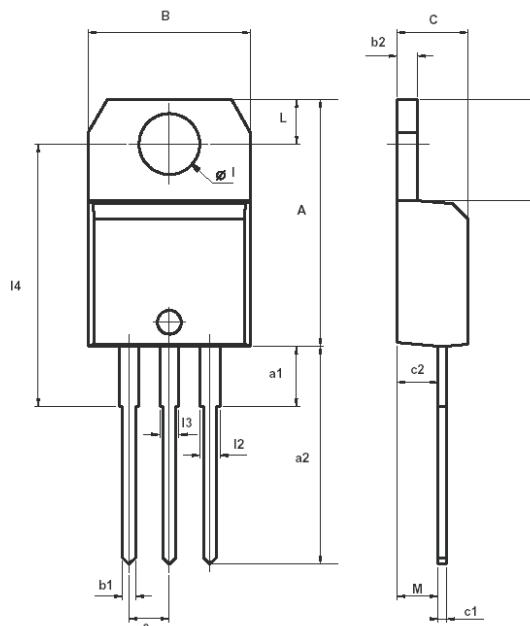


Fig. 9: On-state characteristics (maximum values).



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MECHANICAL DATA

Dimensions in mm
Net Mass: 2 g



REF.	DIMENSIONS		
	Millimeters		
	Min.	Typ.	Max.
A	15.2		15.9
a1	3.2		3.95
a2	13.00		14.00
B	10.00		10.40
b1	0.61		0.88
b2	1.20		1.32
C	4.40		4.6
c1	0.45		0.7
c2	2.20		2.72
e	2.30		2.70
f	6.20		6.60
I	3.70		3.85
I4	15.80		16.8
L	2.65		2.95
I2	1.14		1.70
I3	1.14		1.70
M	2.47		2.73